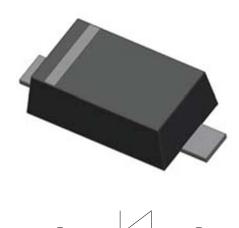






# **Schottky Barrier Diode**



#### **Features**

Moisture sensitivity level 1

• Reverse voltage: 30V

• Average forward current : 200mA

### **Application**

High frequency and low voltage rectifier

#### **Mechanical data**

• Package: SOD-523

• Terminals: Tin plated leads, solderable per

J-STD-002 and JESD22-B102

## ■ Maximum Ratings (Ta=25°C Unless otherwise specified)

Parameter	Symbol	Unit	Value
Device marking code			В
Reverse voltage	V <sub>R</sub>	V	30
Forward current	I <sub>F</sub>	mA	200
Non-repetitive surge peak forward current @ t=8.3ms half-sine wave		٨	1
Non-repetitive surge peak forward current @ t=1ms square wave	I <sub>FSM</sub>	А	2.5
Power dissipation	P <sub>D</sub>	mW	150
Junction temperature	TJ	°C	-40 to +125
Storage temperature	$T_{STG}$	°C	-40 to +125







## ■ Electrical Characteristics (T<sub>a</sub>=25°C Unless otherwise specified)

Parameter	Symbol	Unit	Conditions	Min	Тур	Max
Breakdown voltage	$V_R$	V	I <sub>R</sub> =500uA	30		
Forward voltage	V <sub>F</sub>	V	I <sub>F</sub> =200mA			0.6
Reverse leakage current	I <sub>R</sub>	uA	V <sub>R</sub> =10V			1

#### ■ Thermal Characteristics

Parameter	Symbol	Unit	Value
Thermal resistance, junction-to-ambient	R <sub>0</sub> J-A <sup>(1)</sup>	°C/W	667
Thermal resistance, junction-to-case	R <sub>0</sub> J-C <sup>(1)</sup>	°C/W	533

#### Note:

(1) Thermal resistance from junction to ambient and from junction to case mounted on P.C.B. with 8mm\*9mm copper pad areas



#### **■**Characteristics

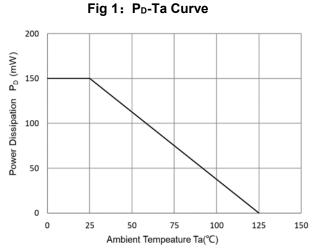


Fig 3: Typical Forward Characteristics

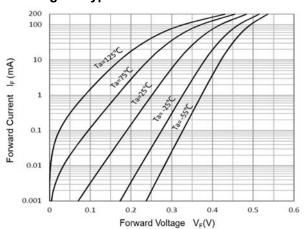


Fig 2: Capacitance Capability

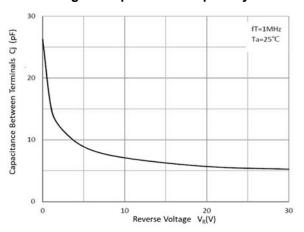
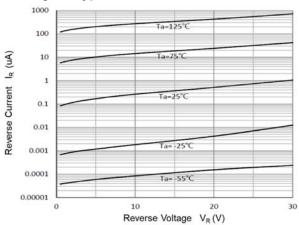


Fig 4: Typical Reverse Characteristics



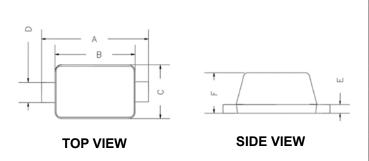




## **■**Ordering Information

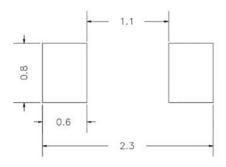
Preferred P/N	Packing code	Unit weight(g)	Minimum package(pcs)	Inner box quantity(pcs)	Outer carton quantity(pcs)	Delivery mode
RB520S-30	F2	Approximate 0.002	8000	80000	320000	7" reel
RB520S-30	F3	Approximate 0.002	3000	30000	120000	7" reel

### **■ Outline Dimensions**



DIMENSIONS					
DIM	INC	HES	ММ		
	MIN	MAX	MN	MAX	
А	0.059	0.067	1.500	1.700	
В	0.043	0.051	1.100	1.300	
С	0.028	0.035	0.700	0.900	
D	0.010	0.014	0.250	0.350	
E	0.002	0.008	0.050	0.200	
F	0.020	0.028	0.500	0.700	

# ■ Suggested Pad Layout



**UNIT:** mm



### **RB520S-30**



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